Amendments to the Specification

Page 10, please replace the paragraph spanning lines 23-32 with the following rewritten paragraph:

The sputtering apparatus was ~~evaluated~~ evacuated until the inside pressure became 2.0 x 10^{-6} Torr or lower and then, after introducing therein 300 sccm of a nitrogen gas and 100 sccm of an oxygen gas, sputtering was carried out in the atmosphere of the film-forming pressure of about 2.3 mTorr at a sputtering electric power of 7.0 kW for 615 seconds. In this case, the temperature of the substrate was about 200°C. By the reactive gas sputtering using the above-described nickel-molybdenum alloy as the target, a first layer (11) was formed on a transparent glass substrate (3) at a thickness of 41 nm as shown in Fig. 3.

Page 11, please replace the paragraph spanning line 33 through page 12, line 7 with the following rewritten paragraph:

The sputtering apparatus was ~~evaluated~~ evacuated until the inside pressure became 2.0 x 10^{-6} Torr or lower and then, after introducing 340 sccm of a nitrogen gas and 60 sccm of an oxygen gas into the sputtering apparatus, sputtering was carried out in the atmosphere of the film-forming pressure of about 2.3 mTorr at a sputtering electric power of 8.3 kW for 195 seconds. Also, in this case, the temperature of the substrate was about 200°C. By the reactive gas sputtering using the above-described nickel-tungsten alloy as the target, a first layer (11) was formed on a transparent glass (3) at a thickness of 17 nm as shown in Fig. 4.

Page 13, please replace the paragraph spanning lines 6-16 with the following rewritten paragraph:

The sputtering apparatus was ~~evaluated~~ evacuated until the inside pressure became 2.0 x 10^{-6} Torr or lower and then, after introducing 240 sccm of a nitrogen gas , 80 sccm of an oxygen gas, and 80 sccm of an argon gas into the sputtering apparatus, sputtering was carried out in the atmosphere of the film-forming pressure of about 2.5 mTorr at a sputtering electric power of 6.0 kW for 330 seconds. In this case, the

temperature of the substrate was about 200°C. Also, in this case, by the reactive gas sputtering using the above-described nickel-copper alloy as the target, a first layer (1) was formed on a transparent glass (3) at a thickness of 45 nm as shown in Fig. 1 of the accompanying drawing.